Year 1
- Lithography and fabrication techniques
- Etching (RIE, Ion Milling)
- Patterned Media
- Transport properties
- Magnetic-semiconductor structure (MSS)
- Magnetic nanostructure modelling

Year 2
- Sub-100 nm structures
- 30 nm structures
- New Recipes
- Successful characterisation
- 100 Gbit/in², properties of single structures
- 200 Gbit/in², interaction between arrays
- Temperature variation
- Single electron tunneling

Year 3
- Sub-10 nm structures, 1 Tbit/cm²
- 30 nm structures
- Successful characterisation
- novel variation
- > 400 Gbit/in², magnetostatic interaction limit

Future
- Sub-10 nm structures
- 1 Tbit/cm²
- New Recipes
- Successful characterisation
- novel variation
- > 400 Gbit/in², magnetostatic interaction limit

Legend:
- Main Research programme
- Supporting research areas
- Research goals